Kazhuhiko Endo

List of Publications by Year
in descending order

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195	3,128	27	47
papers	citations	h-index	g-index
		201575	214721

195	195	195	2257
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Room-temperature and high-quality HfO2/SiO2 gate stacked film grown by neutral beam enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .	0.9	7
2	High Electron Mobility Germanium FinFET Fabricated by Atomic Layer Defect-Free and Roughness-Free Etching. IEEE Open Journal of Nanotechnology, 2021, 2, 26-30.	0.9	8
3	Si Nanopillar/SiGe Composite Structure for Thermally Managed Nano-devices. , 2021, , .		2
4	Management of Phonon Transport in Lateral Direction for Gap-Controlled Si Nanopillar/SiGe Interlayer Composite Materials. IEEE Open Journal of Nanotechnology, 2021, 2, 148-152.	0.9	2
5	Correction to â€œAnalytical Thermal Model for Self-Heating in Advanced FinFET Devices With Implications for Design and Reliabilityâ€. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2020, 39, 277-277.	1.9	0
6	Highly Water-Repellent Nanostructure on Quartz Surface Based on Cassie-Baxter Model With Filling Factor. IEEE Open Journal of Nanotechnology, 2020, 1, 1-5.	0.9	1
7	Performance improvement of Ge fin field-effect transistors by post-fin-fabrication annealing. Japanese Journal of Applied Physics, 2020, 59, SIIE05.	0.8	0
8	Atomic layer defect-free etching for germanium using HBr neutral beam. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, 051001.	0.9	4
9	Microwave Annealing Technologies for Variability Reduction of Nanodevices: A Review of Their Impact on FinFETs. IEEE Nanotechnology Magazine, 2019, 13, 34-38.	0.9	1
10	The 2D Materials Used for Nanodevice Applications: Utilizing Aggressively Scaled Transistors. IEEE Nanotechnology Magazine, 2019, 13, 39-42.	0.9	0
11	Atomic layer germanium etching for 3D Fin-FET using chlorine neutral beam. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	0.9	15
12	Steep switching less than 15 mV dec^{âˆ’1} in silicon-on-insulator tunnel FETs by a trimmed-gate structure. Japanese Journal of Applied Physics, 2019, 58, SBBA16.	0.8	8
13	Multidomain Dynamics of Ferroelectric Polarization and its Coherency-Breaking in Negative Capacitance Field-Effect Transistors. , 2018, , .		9
14	Steep switching in trimmed-gate tunnel FET. AIP Advances, 2018, 8, .	0.6	5
15	Enhancement of capacitance benefit by drain offset structure in tunnel field-effect transistor circuit speed associated with tunneling probability increase. Japanese Journal of Applied Physics, 2018, 57, 04FD13.	0.8	1
16	On the drain bias dependence of long-channel silicon-on-insulator-based tunnel field-effect transistors. Japanese Journal of Applied Physics, 2017, 56, 04CD04.	0.8	2
17	Tunnel FinFET CMOS inverter with very low short-circuit current for ultralow-power Internet of Things application. Japanese Journal of Applied Physics, 2017, 56, 04CD19.	0.8	15
18	Bias temperature instability in tunnel field-effect transistors. Japanese Journal of Applied Physics, 2017, 56, 04CA04.	0.8	2

#	Article	IF	Citations
19	Impacts of plasma-induced damage due to UV light irradiation during etching on Ge fin fabrication and device performance of Ge fin field-effect transistors. Applied Physics Express, 2017, 10, 026501.	1.1	33
20	Advanced FinFET technologies for boosting SRAM performance. , 2017, , .		0
21	Spike-based time-domain weighted-sum calculation using nanodevices for low power operation. , 2016, , .		6
22	Defect-free germanium etching for 3D Fin MOSFET using neutral beam etching. , 2016, , .		1
23	Silicon nanodisk array with a fin field-effect transistor for time-domain weighted sum calculation toward massively parallel spiking neural networks. Applied Physics Express, 2016, 9, 034201.	1.1	14
24	Introduction of SiGe/Si heterojunction into novel multilayer tunnel FinFET. Japanese Journal of Applied Physics, 2016, 55, 04EB06.	0.8	15
25	Heated ion implantation for high-performance and highly reliable silicon-on-insulator complementary metalâ€“oxideâ€“silicon fin field-effect transistors. Japanese Journal of Applied Physics, 2015, 54, 04DA06.	0.8	4
26	Inhibition of enamel demineralization and bond-strength properties of bioactive glass containing 4-META/MMA-TBB-based resin adhesive. European Journal of Oral Sciences, 2015, 123, 202-207.	0.7	27
27	Impact of granular work function variation in a gate electrode on low-frequency noise for fin field-effect transistors. Applied Physics Express, 2015, 8, 044201.	1.1	7
28	Impact of fin length on threshold voltage modulation by back bias for Independent double-gate tunnel fin field-effect transistors. Solid-State Electronics, 2015, 111, 62-66.	0.8	3
29	Highly Vt tunable and low variability triangular fin-channel MOSFETs on SOTB. Microelectronic Engineering, 2015, 147, 290-293.	1.1	0
30	Improvement of epitaxial channel quality on heavily arsenic- and boron-doped Si surfaces and impact on performance of tunnel field-effect transistors. Solid-State Electronics, 2015, 113, 173-178.	0.8	6
31	Channel shape and interpoly dielectric material effects on electrical characteristics of floating-gate-type three-dimensional fin channel flash memories. Japanese Journal of Applied Physics, 2015, 54, 04DD04.	0.8	2
32	Comparative Study of Charge Trapping Type SOI-FinFET Flash Memories with Different Blocking Layer Materials. Journal of Low Power Electronics and Applications, 2014, 4, 153-167.	1.3	5
33	Scaling breakthrough for analog/digital circuits by suppressing variability and low-frequency noise for FinFETs by amorphous metal gate technology. , 2014, , .		4
34	Responses of RAW264.7 macrophages to waterâ€dispersible gold and silver nanoparticles stabilized by metalâ€“carbon Ïƒâ€bonds. Journal of Biomedical Materials Research - Part A, 2014, 102, 1838-1849.	2.1	18
35	Inhibition of enamel demineralization by buffering effect of Sâ€<scp>PRG</scp> fillerâ€containing dental sealant. European Journal of Oral Sciences, 2014, 122, 78-83.	0.7	83
36	Influence of work function variation of metal gates on fluctuation of sub-threshold drain current for fin field-effect transistors with undoped channels. Japanese Journal of Applied Physics, 2014, 53, 04EC11.	0.8	12

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37	Experimental study of three-dimensional fin-channel charge trapping flash memories with titanium nitride and polycrystalline silicon gates. Japanese Journal of Applied Physics, 2014, 53, 04ED16.	0.8	2
38	Performance Enhancement of Tunnel Field-Effect Transistors by Synthetic Electric Field Effect. IEEE Electron Device Letters, 2014, 35, 792-794.	2.2	53
39	Performance evaluation of parallel electric field tunnel field-effect transistor by a distributed-element circuit model. Solid-State Electronics, 2014, 102, 82-86.	0.8	7
40	Robust FinFET SRAM design based on dynamic back-gate voltage adjustment. Microelectronics Reliability, 2014, 54, 2604-2612.	0.9	14
41	Analysis of Threshold Voltage Flexibility in Ultrathin-BOX SOI FinFETs. Journal of Low Power Electronics and Applications, 2014, 4, 110-118.	1.3	1
42	Experimental study of charge trapping type FinFET flash memory. , 2014, , .		0
43	Analytical Thermal Model for Self-Heating in Advanced FinFET Devices With Implications for Design and Reliability. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2013, 32, 1045-1058.	1.9	57
44	Frictional and mechanical properties of diamond-like carbon-coated orthodontic brackets. European Journal of Orthodontics, 2013, 35, 216-222.	1.1	23
45	1/fNoise Characteristics of Fin-Type Field-Effect Transistors in Saturation Region. Japanese Journal of Applied Physics, 2013, 52, 04CC23.	0.8	0
46	Gate Structure Dependence of Variability in Polycrystalline Silicon Fin-Channel Flash Memories. Japanese Journal of Applied Physics, 2013, 52, 06GE01.	0.8	3
47	Atomic Layer Deposition of SiO₂ for the Performance Enhancement of Fin Field Effect Transistors. Japanese Journal of Applied Physics, 2013, 52, 116503.	0.8	8
48	Suppression of threshold voltage variability of double-gate fin field-effect transistors using amorphous metal gate with uniform work function. Applied Physics Letters, 2013, 102, .	1.5	15
49	Independent-Double-Gate FinFET SRAM Technology. IEICE Transactions on Electronics, 2013, E96.C, 413-423.	0.3	1
50	Fabrication of Floating-Gate-Type Fin-Channel Double- and Tri-Gate Flash Memories and Comparative Study of Their Electrical Characteristics. Japanese Journal of Applied Physics, 2012, 51, 04DD03.	0.8	2
51	Fabrication and Characterization of NOR-Type Tri-Gate Flash Memory with Improved Inter-Poly Dielectric Layer by Rapid Thermal Oxidation. Japanese Journal of Applied Physics, 2012, 51, 06FE19.	0.8	6
52	Experimental Study of Floating-Gate-Type Metalâ€“Oxideâ€“Semiconductor Capacitors with Nanosize Triangular Cross-Sectional Tunnel Areas for Low Operating Voltage Flash Memory Application. Japanese Journal of Applied Physics, 2012, 51, 06FF01.	0.8	2
53	Experimental Comparisons between Tetrakis(dimethylamino)titanium Precursor-Based Atomic-Layer-Deposited and Physical-Vapor-Deposited Titaniumâ€“Nitride Gate for High-Performance Fin-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DA05.	0.8	0
54	(Invited) On-Current Variability Sources of FinFETs: Analysis and Perspective for 14nm-Lg Technology. ECS Transactions, 2012, 45, 231-242.	0.3	0

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55	Experimental study of tri-gate SOI-FinFET flash memory. , 2012, , .		1
56	Flexible V<inf>th</inf> FinFETs with 9-nm-thick extremely-thin BOX. , 2012, , .		1
57	Suppressing V<inf>t</inf> and G<inf>m</inf> variability of FinFETs using amorphous metal gates for 14 nm and beyond. , 2012, , .		22
58	Cryogenic operation of double-gate FinFET and demonstration of analog circuit at 4.2K. , 2012, , .		2
59	Enhancement of FinFET performance using 25-nm-thin sidewall spacer grown by atomic layer deposition. Solid-State Electronics, 2012, 74, 13-18.	0.8	13
60	Demonstration of Split-Gate Type Trigate Flash Memory With Highly Suppressed Over-Erase. IEEE Electron Device Letters, 2012, 33, 345-347.	2.2	10
61	Variability Origins of Parasitic Resistance in FinFETs With Silicided Source/Drain. IEEE Electron Device Letters, 2012, 33, 474-476.	2.2	15
62	Variability Analysis of Scaled Crystal Channel and Poly-Si Channel FinFETs. IEEE Transactions on Electron Devices, 2012, 59, 573-581.	1.6	12
63	Fin-Height Effect on Poly-Si/PVD-TiN Stacked-Gate FinFET Performance. IEEE Transactions on Electron Devices, 2012, 59, 647-653.	1.6	14
64	A Correlative Analysis Between Characteristics of FinFETs and SRAM Performance. IEEE Transactions on Electron Devices, 2012, 59, 1345-1352.	1.6	3
65	Decomposition of On-Current Variability of nMOS FinFETs for Prediction Beyond 20 nm. IEEE Transactions on Electron Devices, 2012, 59, 2003-2010.	1.6	27
66	High-Frequency Precise Characterization of Intrinsic FinFET Channel. IEICE Transactions on Electronics, 2012, E95.C, 752-760.	0.3	1
67	Fabrication and Characterization of NOR-Type Tri-Gate Flash Memory with Improved Inter-Poly Dielectric Layer by Rapid Thermal Oxidation. Japanese Journal of Applied Physics, 2012, 51, 06FE19.	0.8	2
68	A 0.7-V Opamp in Scaled Low-Standby-Power FinFET Technology. IEICE Transactions on Electronics, 2012, E95.C, 686-695.	0.3	0
69	Fabrication of Floating-Gate-Type Fin-Channel Double- and Tri-Gate Flash Memories and Comparative Study of Their Electrical Characteristics. Japanese Journal of Applied Physics, 2012, 51, 04DD03.	0.8	1
70	Experimental Comparisons between Tetrakis(dimethylamino)titanium Precursor-Based Atomic-Layer-Deposited and Physical-Vapor-Deposited Titaniumâ€“Nitride Gate for High-Performance Fin-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DA05.	0.8	2
71	Experimental Study of Floating-Gate-Type Metalâ€“Oxideâ€“Semiconductor Capacitors with Nanosize Triangular Cross-Sectional Tunnel Areas for Low Operating Voltage Flash Memory Application. Japanese Journal of Applied Physics, 2012, 51, 06FF01.	0.8	1
72	Comparative study of tri-gate flash memories with split and stack gates. , 2011, , .		1

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73	Influence of fin height on poly-Si/PVD-TiN stacked gate FinFET performance. , 2011, , .		0
74	Influence of NiSi on parasitic resistance fluctuation of FinFETs. , 2011, , .		4
75	Variability analysis of scaled poly-Si channel FinFETs and tri-gate flash memories for high density and low cost stacked 3D-memory application. , 2011, , .		1
76	Variability origins of FinFETs and perspective beyond 20nm node. , 2011, , .		3
77	Advanced FinFET process technology for 20 nm node and beyond. , 2011, , .		7
78	Atomic layer deposition of 25-nm-thin sidewall spacer for enhancement of FinFET performance. , 2011, , .		2
79	Independent double-gate FinFET SRAM technology. , 2011, , .		4
80	Grain-Orientation Induced Quantum Confinement Variation in FinFETs and Multi-Gate Ultra-Thin Body CMOS Devices and Implications for Digital Design. IEEE Transactions on Electron Devices, 2011, 58, 2282-2292.	1.6	17
81	A review: Biodegradation of resinâ€"dentin bonds. Japanese Dental Science Review, 2011, 47, 5-12.	2.0	40
82	Comprehensive analysis of I<inf>on</inf> variation in metal gate FinFETs for 20nm and beyond. , 2011, , .		7
83	Correlative analysis between characteristics of 30-nm L<inf>G</inf> FinFETs and SRAM performance. , 2011, , .		1
84	Low activation energy, high-quality oxidation of Si and Ge using neutral beam. Applied Physics Letters, 2011, 98, 203111.	1.5	21
85	Experimental Study of Physical-Vapor-Deposited Titanium Nitride Gate with An n⁺-Polycrystalline Silicon Capping Layer and Its Application to 20 nm Fin-Type Double-Gate Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC14.	0.8	12
86	Experimental Study of Physical-Vapor-Deposited Titanium Nitride Gate with An n+-Polycrystalline Silicon Capping Layer and Its Application to 20 nm Fin-Type Double-Gate Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC14.	0.8	6
87	Corrosion behavior of ion implanted nickel-titanium orthodontic wire in fluoride mouth rinse solutions. Dental Materials Journal, 2010, 29, 53-58.	0.8	28
88	Grain-Orientation Induced Work Function Variation in Nanoscale Metal-Gate Transistorsâ€"Part I: Modeling, Analysis, and Experimental Validation. IEEE Transactions on Electron Devices, 2010, 57, 2504-2514.	1.6	156
89	Grain-Orientation Induced Work Function Variation in Nanoscale Metal-Gate Transistorsâ€"Part II: Implications for Process, Device, and Circuit Design. IEEE Transactions on Electron Devices, 2010, 57, 2515-2525.	1.6	78
90	Design Optimization of FinFET Domino Logic Considering the Width Quantization Property. IEEE Transactions on Electron Devices, 2010, 57, 2934-2943.	1.6	29

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91	Design of SOI FinFET on 32nm technology node for low standby power (LSTP) operation considering gate-induced drain leakage (GIDL). Solid-State Electronics, 2010, 54, 1060-1065.	0.8	7
92	Tenâ€year degradation of resinâ€"dentin bonds. European Journal of Oral Sciences, 2010, 118, 404-410.	0.7	56
93	Crystal growth by restorative filling materials. European Journal of Oral Sciences, 2010, 118, 489-493.	0.7	10
94	Investigation of Low-Energy Tilted Ion Implantation for Fin-Type Double-Gate Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistor Extension Doping. Japanese Journal of Applied Physics, 2010, 49, 04DC18.	0.8	22
95	Minimization of Gate-Induced Drain Leakage by Controlling Gate Underlap Length for Low-Standby-Power Operation of 20-nm-Level Four-Terminal Silicon-on-Insulator Fin-Shaped Field Effect Transistor. Japanese Journal of Applied Physics, 2010, 49, 024203.	0.8	0
96	Investigation of Thermal Stability of TiN Film Formed by Atomic Layer Deposition Using Tetrakis(dimethylamino)titanium Precursor for Metal-Gate Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2010, 49, 04DA16.	0.8	7
97	Variability Analysis of TiN Metal-Gate FinFETs. IEEE Electron Device Letters, 2010, 31, 546-548.	2.2	63
98	Realization of 0.7-V analog circuits by adaptive-Vt operation of FinFET. , 2010, , .		1
99	High-frequency characterization of intrinsic FinFET channel. , 2010, , .		3
100	Low resistive ALD TiN metal gate using TDMAT precursor for high performance MOSFET. , 2010, , .		0
101	Variability analysis of TiN FinFET SRAM cell performance and its compensation using Vth-controllable independent double-gate FinFET. , 2010, , .		0
102	Variability Analysis of TiN FinFET SRAM Cells and Its Compensation by Independent-DG FinFETs. IEEE Electron Device Letters, 2010, 31, 1095-1097.	2.2	4
103	0.5V FinFET SRAM with dynamic threshold control of pass gates for salvaging malfunctioned bits. , 2010, , .		1
104	Fin-height controlled PVD-TiN gate finFET SRAM for enhancing noise margin. , 2010, , .		3
105	Optimization of RTA process for PVD-TiN gate FinFETs. , 2010, , .		0
106	Nanoscale Wet Etching of Physical-Vapor-Deposited Titanium Nitride and Its Application to Sub-30-nm-Gate-Length Fin-Type Double-Gate Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistor Fabrication. Japanese Journal of Applied Physics, 2010, 49, 06GH18.	0.8	27
107	May the fourth (terminal) be with you - circuit design beyond FinFET. , 2010, , .		1
108	On the gate-stack origin threshold voltage variability in scaled FinFETs and multi-FinFETs. , 2010, , .		32

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109	Independent-Double-Gate FINFET SRAM Cell for Drastic Leakage Current Reduction. Lecture Notes in Electrical Engineering, 2010, , 67-79.	0.3	0
110	Enhancing Noise Margins of Fin-Type Field Effect Transistor Static Random Access Memory Cell by Using Threshold Voltage-Controllable Flexible-Pass-Gates. Applied Physics Express, 2009, 2, 054502.	1.1	4
111	Experimental evaluation of parallel transmission using optical ZCZ-CDMA system. , 2009, , .		2
112	Nanoscale TiN wet etching and its application for FinFET fabrication. , 2009, , .		2
113	Variation analysis of TiN FinFETs. , 2009, , .		12
114	Low Temperature, Beam-Orientation-Dependent, Lattice-Plane-Independent, and Damage-Free Oxidation for Three-Dimensional Structure by Neutral Beam Oxidation. Japanese Journal of Applied Physics, 2009, 48, 04C007.	0.8	21
115	Reduction of Moisture in Semiconductor Dry Process Equipment by Generating Extremely Low Oxygen Ambience. Japanese Journal of Applied Physics, 2009, 48, 08HH01.	0.8	0
116	A Comparative Study of Nitrogen Gas Flow Ratio Dependence on the Electrical Characteristics of Sputtered Titanium Nitride Gate Bulk Planar Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors and Fin-Type Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2009, 48, 05DC01.	0.8	23
117	Vertical ultrathinâ€channel multiâ€gate MOSFETs (MuGFETs): technological challenges and future developments. IEEJ Transactions on Electrical and Electronic Engineering, 2009, 4, 386-391.	0.8	2
118	<i>In vitro</i> degradation of resinâ€"dentin bonds with oneâ€bottle selfâ€etching adhesives. European Journal of Oral Sciences, 2009, 117, 611-617.	0.7	35
119	Dual metal gate FinFET integration by Ta/Mo diffusion technology for Vt reduction and multi-Vt CMOS application. Solid-State Electronics, 2009, 53, 701-705.	0.8	3
120	Fluctuation Analysis of Parasitic Resistance in FinFETs With Scaled Fin Thickness. IEEE Electron Device Letters, 2009, 30, 407-409.	2.2	23
121	Design of SOI FinFET on 32 nm technology node for low standby power (LSTP) operation considering gate-induced drain leakage (GIDL). , 2009, , .		0
122	Independent-Double-Gate FinFET SRAM for Leakage Current Reduction. IEEE Electron Device Letters, 2009, 30, 757-759.	2.2	24
123	Impact of FinFET technology on 6T-SRAM performance. , 2009, , .		0
124	Effect of dentinal water on bonding of self-etching adhesives. Dental Materials Journal, 2009, 28, 634-641.	0.8	17
125	Threshold-Voltage Reduction of FinFETs by Ta/Mo Interdiffusion Dual Metal-Gate Technology for Low-Operating-Power Application. IEEE Transactions on Electron Devices, 2008, 55, 2454-2461.	1.6	12
126	Independent-gate four-terminal FinFET SRAM for drastic leakage current reduction. , 2008, , .		1

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127	An experimental study of TiN gate FinFET SRAM with (111)-oriented sidewall channels. , 2008, , .		0
128	Enhancing SRAM cell performance by using independent double-gate FinFET. , 2008, , .		30
129	Variable-Threshold-Voltage FinFETs with a Control-Voltage Range within the Logic-Level Swing Using Asymmetric Work-Function Double Gates. International Power Modulator Symposium and High-Voltage Workshop, 2008, , .	0.0	0
130	Enhancing noise margins of FinFET SRAM by integrating V<inf>th</inf>-controllable flexible-pass-gates. , 2008, , .		3
131	Impact of extension and source/drain resistance on FinFET performance. , 2008, , .		6
132	A Ta/Mo Interdiffusion Dual Metal Gate Technology for Drivability Enhancement of FinFETs. IEEE Electron Device Letters, 2008, 29, 618-620.	2.2	9
133	Modeling and analysis of grain-orientation effects in emerging metal-gate devices and implications for SRAM reliability. , 2008, , .		87
134	Dual-Metal-Gate Transistors with Symmetrical Threshold Voltages Using Work-Function-Tuned Ta/Mo Bilayer Metal Gates. Japanese Journal of Applied Physics, 2008, 47, 2428-2432.	0.8	4
135	Nitrogen Gas Flow Ratio and Rapid Thermal Annealing Temperature Dependences of Sputtered Titanium Nitride Gate Work Function and Their Effect on Device Characteristics. Japanese Journal of Applied Physics, 2008, 47, 2433.	0.8	20
136	Ta/Mo Stack Dual Metal Gate Technology Applicable to Gate-First Processes. Japanese Journal of Applied Physics, 2007, 46, 1825-1829.	0.8	4
137	Application of Plasma Immersion Ion Implantation for Surface Modification of Nickel-titanium Rotary Instruments. Dental Materials Journal, 2007, 26, 467-473.	0.8	21
138	Experimental Evaluation of Effects of Channel Doping on Characteristics of FinFETs. IEEE Electron Device Letters, 2007, 28, 1123-1125.	2.2	28
139	Modeling and Analysis of Self-Heating in FinFET Devices for Improved Circuit and EOS/ESD Performance. , 2007, , .		33
140	Cointegration of High-Performance Tied-Gate Three-Terminal FinFETs and Variable Threshold-Voltage Independent-Gate Four-Terminal FinFETs With Asymmetric Gate-Oxide Thicknesses. IEEE Electron Device Letters, 2007, 28, 517-519.	2.2	48
141	A Dynamical Power-Management Demonstration Using Four-Terminal Separated-Gate FinFETs. IEEE Electron Device Letters, 2007, 28, 452-454.	2.2	9
142	Four-Terminal FinFETs Fabricated Using an Etch-Back Gate Separation. IEEE Nanotechnology Magazine, 2007, 6, 201-205.	1.1	18
143	A Dynamical Power-Management Demonstration Using Four-Terminal Separated-Gate FinFETs. SOI Conference, Proceedings of the IEEE International, 2006, , .	0.0	1
144	Investigation of the TiN Gate Electrode With Tunable Work Function and Its Application for FinFET Fabrication. IEEE Nanotechnology Magazine, 2006, 5, 723-730.	1.1	90

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145	Vertical Double-Gate MOSFET Device Technology. IEEJ Transactions on Electronics, Information and Systems, 2006, 126, 702-707.	0.1	0
146	A novel method for the 3-dimensional simulation of orthognathic surgery by using a multimodal image-fusion technique. American Journal of Orthodontics and Dentofacial Orthopedics, 2006, 130, 786-798.	0.8	100
147	Fabrication of FinFETs by Damage-Free Neutral-Beam Etching Technology. IEEE Transactions on Electron Devices, 2006, 53, 1826-1833.	1.6	37
148	Investigation of N-Channel Triple-Gate Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors on (100) Silicon On Insulator Substrate. Japanese Journal of Applied Physics, 2006, 45, 3097-3100.	0.8	8
149	Demonstration and Analysis of Accumulation-Mode Double-Gate Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2006, 45, 3079-3083.	0.8	5
150	Experimental Study of Effective Carrier Mobility of Multi-Fin-Type Double-Gate Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors with (111) Channel Surface Fabricated by Orientation-Dependent Wet Etching. Japanese Journal of Applied Physics, 2006, 45, 3084-3087.	0.8	18
151	Deoxidization of Cu Oxide under Extremely Low Oxygen Pressure Ambient. Japanese Journal of Applied Physics, 2006, 45, L393-L395.	0.8	10
152	New Fabrication Technology of Fin Field Effect Transistors Using Neutral-Beam Etching. Japanese Journal of Applied Physics, 2006, 45, 5513-5516.	0.8	5
153	Fabrication of a Vertical-Channel Double-Gate Metal-Oxide-Semiconductor Field-Effect Transistor Using a Neutral Beam Etching. Japanese Journal of Applied Physics, 2006, 45, L279-L281.	0.8	9
154	Advanced FinFET CMOS Technology: TiN-Gate, Fin-Height Control and Asymmetric Gate Insulator Thickness 4T-FinFETs. , 2006, , .		28
155	Fabrication and characterization of vertical-type double-gate metal-oxide-semiconductor field-effect transistor with ultrathin Si channel and self-aligned source and drain. Applied Physics Letters, 2006, 88, 072103.	1.5	7
156	Galvanic corrosion behavior of orthodontic archwire alloys coupled to bracket alloys. Angle Orthodontist, 2006, 76, 705-11.	1.1	27
157	Work function controllability of metal gates made by interdiffusing metal stacks with low and high work functions. Microelectronic Engineering, 2005, 80, 284-287.	1.1	12
158	Demonstration, Analysis, and Device Design Considerations for Independent DG MOSFETs. IEEE Transactions on Electron Devices, 2005, 52, 2046-2053.	1.6	115
159	Demonstration of Dopant Profiling in Ultrathin Channels of Vertical-Type Double-Gate Metal-Oxide-Semiconductor Field-Effect-Transistor by Scanning Nonlinear Dielectric Microscopy. Japanese Journal of Applied Physics, 2005, 44, 2400-2404.	0.8	2
160	A new fabrication technology of FinFETs using a neutral beam etching. , 2005, , .		0
161	Metal Organic Atomic Layer Deposition of Metal Silicate Film for High-kGate Dielectrics. Japanese Journal of Applied Physics, 2004, 43, L1296-L1298.	0.8	2
162	Dopant profiling in vertical ultrathin channels of double-gate metalâ€"oxideâ€"semiconductor field-effect transistors by using scanning nonlinear dielectric microscopy. Applied Physics Letters, 2004, 85, 4139-4141.	1.5	22

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163	In Vitro Corrosion Characteristics of Commercially Available Orthodontic Wires. Dental Materials Journal, 2004, 23, 197-202.	0.8	27
164	Electrochemical and surface studies on the passivity of a dental Pd-based casting alloy in alkaline sulphide solution. Corrosion Science, 2003, 45, 1491-1504.	3.0	12
165	Growth by MOMBE of c-axis superconducting YBCO thin films on different substrates: in situ RHEED monitoring of the growth. IEEE Transactions on Applied Superconductivity, 2003, 13, 2792-2794.	1.1	1
166	Metal Organic Atomic Layer Deposition of High-k Gate Dielectrics Using Plasma Oxidation. Japanese Journal of Applied Physics, 2003, 42, L685-L687.	0.8	28
167	Atomic Layer Deposition of High-k Gate Dielectrics Using MO Precursor and Cyclic Plasma Exposure. Materials Research Society Symposia Proceedings, 2002, 745, 281.	0.1	1
168	Preparation by MOCVD and characterization by AFM of the (119) oriented Bi-2223 thin films. Physica C: Superconductivity and Its Applications, 2002, 378-381, 1274-1277.	0.6	2
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